

Linear Systems replaces discontinued Siliconix U309

The LSU309 is a high frequency n-channel JFET offering a wide range and low noise performance. The hermetically sealed TO-18 package is well suited for high reliability and harsh environment applications.

(See Packaging Information).

LSU309 Benefits:

- High Power Low Noise gain
- Dynamic Range greater than 100dB
- Easily matched to 75Ω input

LSU309 Applications:

- UHV / VHF Amplifiers
- Mixers
- Oscillators

FEATURES

DIRECT REPLACEMENT FOR SILICONIX U309

OUTSTANDING HIGH FREQUENCY GAIN $G_{DG} = 11.5\text{dB}$

LOW HIGH FREQUENCY NOISE $NF = 2.7\text{dB}$

ABSOLUTE MAXIMUM RATINGS @ 25°C¹

Maximum Temperatures

Storage Temperature -55°C to +150°C

Operating Junction Temperature -55°C to +135°C

Maximum Power Dissipation

Continuous Power Dissipation 500mW

MAXIMUM CURRENT

Gate Current 10mA

MAXIMUM VOLTAGES

Gate to Drain Voltage or Gate to Source Voltage -25V

LSU309 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNIT	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	-25	--	--	V	$V_{DS} = 0V, I_G = -1\mu A$
$V_{GS(F)}$	Gate to Source Forward Voltage	0.7	--	1		$V_{DS} = 0V, I_G = 10mA$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-1	--	-4		$V_{DS} = 10V, I_D = 1nA$
I_{DSS}	Drain to Source Saturation Current ²	12	--	30	mA	$V_{DS} = 10V, V_{GS} = 0V$
I_G	Gate Operating Current (Note 3)	--	-15	--	pA	$V_{DG} = 9V, I_D = 10mA$
$r_{DS(on)}$	Drain to Source On Resistance	--	35	--	Ω	$V_{GS} = 0V, I_D = 1mA$

LSU309 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNIT	CONDITIONS
g_{fs}	Forward Transconductance	10	14		mS	$V_{DS} = 10V, I_D = 10mA, f = 1kHz$
g_{os}	Output Conductance	--	110	250	μS	
C_{iss}	Input Capacitance	--	4	5	pF	$V_{DS} = 10V, V_{GS} = -10V, f = 1MHz$
C_{rss}	Reverse Transfer Capacitance	--	1.9	2.5		
e_n	Equivalent Noise Voltage	6	--	--	nV/√Hz	$V_{DS} = 10V, I_D = 10mA, f = 100Hz$

LSU309 HIGH FREQUENCY CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNIT	CONDITIONS	
NF	Noise Figure	f = 105MHz	--	1.5	--	dB	$V_{DS} = 10V, I_D = 10mA$
		f = 450MHz	--	2.7	--	dB	
G_{pg}	Power Gain ³	f = 105MHz	--	16	--		
		f = 450MHz	--	11.5	--		
g_{fg}	Forward Transconductance	f = 105MHz	--	14	--	mS	
		f = 450MHz	--	13	--		
g_{og}	Output Conductance	f = 105MHz	--	0.16	--		
		f = 450MHz	--	0.55	--		

Note 1 - Absolute maximum ratings are limiting values above which LSU309 serviceability may be impaired.

Note 2 - Pulse test : $PW \leq 300\mu s$, Duty Cycle $\leq 3\%$

Note 3 - Measured at optimum input noise match

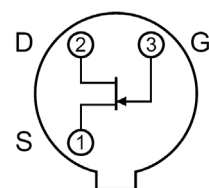
Micross Components Europe

Available Packages:

TO-18 (Bottom View)



LSU309 in TO-18
LSU309 in bare die.



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Please contact Micross for full package and die dimensions